# 全宇昕科技股份有限公司 Cystech Electronics Corp.

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TEL:+886-2-8227-3826

1. MTE020N10RF3 規格書

2. SGS test report for T0-263

FAX:+886-2-8227-3830

# 承認書 FOR APPROVAL

客戶/Customer : 盟創科技股份有限公司 零件類別/Product Name: MOSFET MTE020N10RF3 品名/Part No. 16-220-000008Z 客戶料號 產品編號/Ordering Device MTEO20N1ORF3-0-T7-G 分類/Rank T0-263 外觀/Outline 800 PCS/Tape & Ree1 包裝/Package 一式2份 發行份數/Copies 羅曉琦/Angela 連絡人 承認書內容

	AUTHORIZED	SIGNATURE
	CYSTEK	CUSTOMER
	Cynek data sheet 請勿轉印TEL:(02)82273826 S北縣中和市中正路716第15第2	
DATE:	2021/05/03	DATE: / /

Spec. No. : C745F3 Issued Date : 2017.10.26 Revised Date : 2021.01.07

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#### **N-Channel Enhancement Mode Power MOSFET**

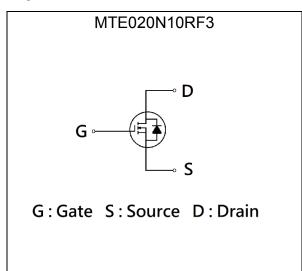
# MTE020N10RF3

#### **Features**

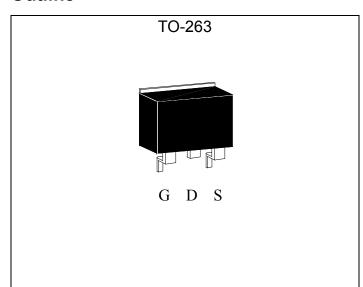
- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package

BVdss	100V
In@V <sub>GS</sub> =10V, T <sub>C</sub> =25°C	24.5A
ID@VGS=10V, TA=25°C	7.5A
RDS(ON)@VGS=10V, ID=20A	$21m\Omega$

#### **Equivalent Circuit**



#### **Outline**



#### **Ordering Information**

Device	Package	Shipping	
MTE020N10RF3-0-T7-G TO-263 (Pb-free lead plating and halogen-free package)		800 pcs / Tape & Reel	
	— Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products		
	— Packing spec, T7: 800 pcs / tape & reel,13" reel		
	— Product rank, zero for no rank products		
	—Product name		



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#### **Absolute Maximum Ratings (TA=25°C)**

Parameter			Symbol	Limits	Unit	
Drain-Source Voltage			$V_{\mathrm{DS}}$	100	V	
Gate-Source Voltage			$V_{GS}$	±20	V	
Continuous Drain Current	t @ V <sub>G</sub> s=10V, T <sub>C</sub> =25°C	*a		24.5		
Continuous Drain Current @ VGs=10V, Tc=100°C *a			T	15.5		
Continuous Drain Current	t @ V <sub>G</sub> s=10V, T <sub>A</sub> =25°C	*b	Id	7.5		
Continuous Drain Current @ V <sub>GS</sub> =10V, T <sub>A</sub> =70°C *b				6	A	
Pulsed Drain Current			Idm	98		
Continuous Body Diode F	Forward Current @ Tc=25°C	*a	Is	20		
Avalanche Current @ L=0	).1mH		Ias	15		
Avalanche Energy @ L=0	.5mH		Eas	25	mJ	
	Tc=25°C	*a		35		
Total Power Dissipation	Tc=100°C	*a	D-	14	W	
	T <sub>A</sub> =25°C	*b	PD	3.3		
	T <sub>A</sub> =70°C	*b		2.1	ı	
Operating Junction and St	orage Temperature Range		TJ, Tstg	-55~+150	°C	

#### **Thermal Data**

Parameter	Symbol	<b>Steady State</b>	Unit
Thermal Resistance, Junction-to-case	RөJC	3.5	0 <i>C/W</i>
Thermal Resistance, Junction-to-ambient *b	RөJA	37	°C/W

#### Note:

<sup>\*</sup>a. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}C$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

<sup>\*</sup>b. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2 oz. copper, in a still air environment with T<sub>A</sub>=25°C. The power dissipation P<sub>D</sub> is based on R<sub>θJA</sub> and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

<sup>\*</sup>c. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and low duty cycles to keep initial T<sub>J</sub>=25°C.



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#### Characteristics (TA=25°C, unless otherwise specified)

Symbol	Min.	Тур.	Max.	Unit	<b>Test Conditions</b>
Static					
BV <sub>DSS</sub>	100	-	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	2	-	4	] V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
$G_{FS}$	-	32	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =20A
Igss	-	-	±100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
I <sub>DSS</sub>	-	-	1	μΑ	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V
R <sub>DS(ON)</sub>	-	21	30	$\mathbf{m}\Omega$	V <sub>GS</sub> =10V, I <sub>D</sub> =20A
Dynamic					
Ciss	-	830	-		
Coss	-	108	-	pF	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz
Crss	-	16	-	1	
Rg	-	1.3	-	Ω	f=1MHz
Qg *1, 2	-	13	-		
Qgs *1, 2	-	5.6	-	nC	V <sub>DS</sub> =50V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V
Qgd *1, 2	-	2.8	-		
td(ON) *1, 2	-	13	-		
tr *1, 2	-	15	-	n a	W 50W I 20A W 10W B 10
t <sub>d(OFF)</sub> *1, 2	-	18	-	ns	V <sub>DS</sub> =50V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V, R <sub>GS</sub> =1 $\Omega$
<b>t</b> f *1, 2	-	6.2	-		
Source-Drain	Diode				
V <sub>SD</sub> *1	-	0.9	1.2	V	I <sub>S</sub> =20A, V <sub>GS</sub> =0V
trr	-	30	-	ns	In=20A dIn/d=100A/ug
Qrr	-	40	-	nC	$-I_F=20A$ , $dI_F/dt=100A/\mu s$

#### Note

<sup>\*1.</sup> Pulse Test : Pulse Width  $\leq$ 300µs, Duty Cycle $\leq$ 2%

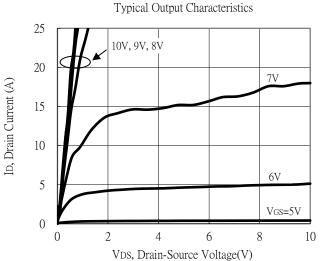
<sup>\*2.</sup> Independent of operating temperature

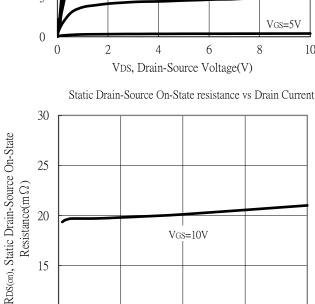


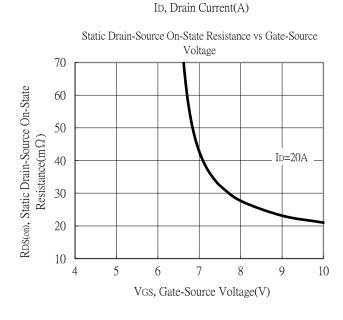
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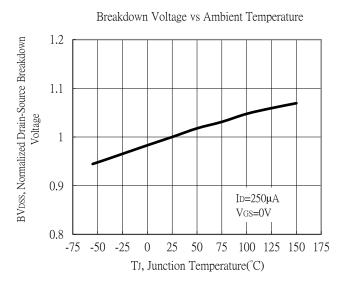
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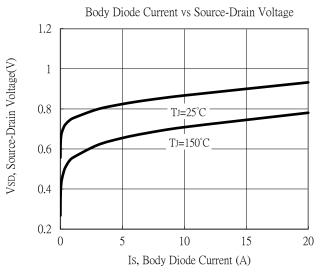
#### **Typical Characteristics**

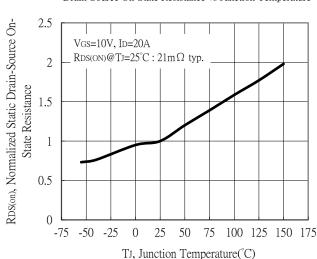












Drain-Source On-State Resistance vs Junction Temperature

15

10

0

5

15

20

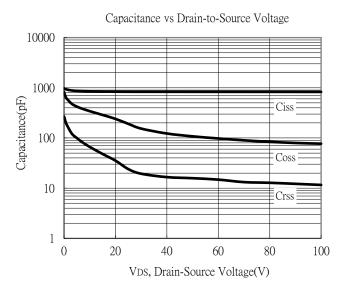
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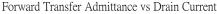


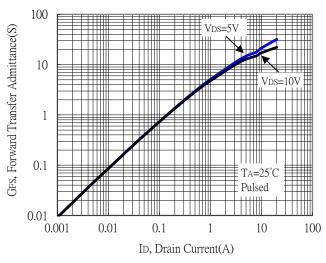
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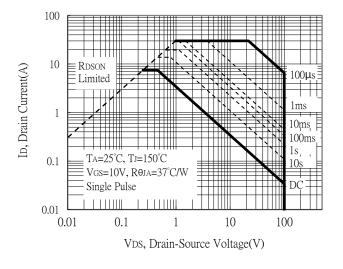
#### **Typical Characteristics (Cont.)**



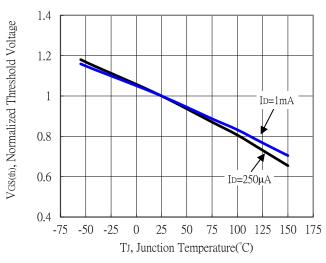




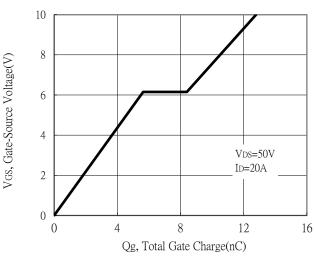
Maximum Safe Operating Area



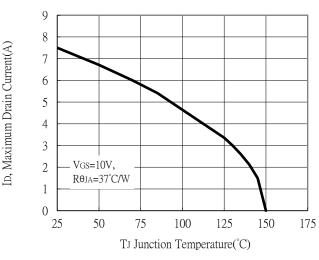
Threshold Voltage vs Junction Temperature



Gate Charge Characteristics



Maximum Drain Current vs Junction Temperature



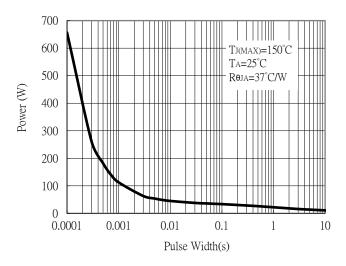


Spec. No. : C745F3 Issued Date : 2017.10.26 Revised Date : 2021.01.07

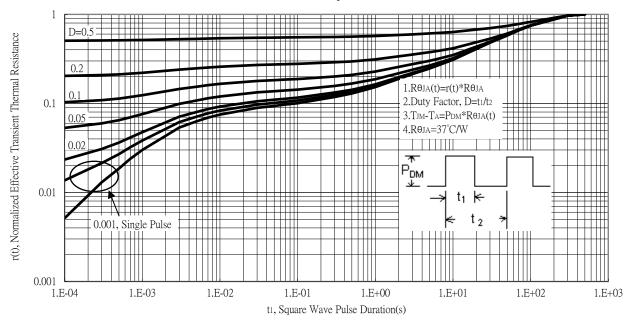
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#### **Typical Characteristics (Cont.)**

Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves

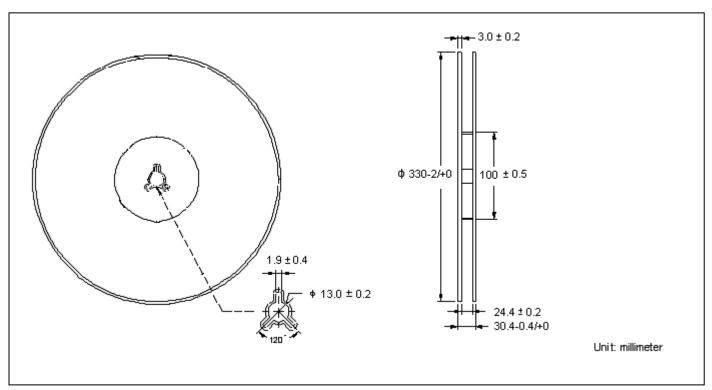




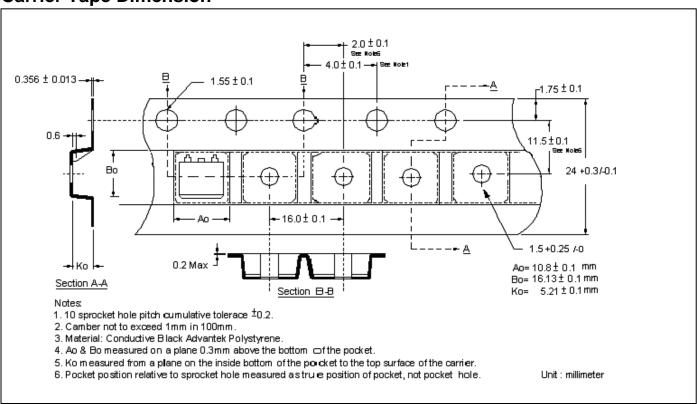
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#### **Reel Dimension**



#### **Carrier Tape Dimension**





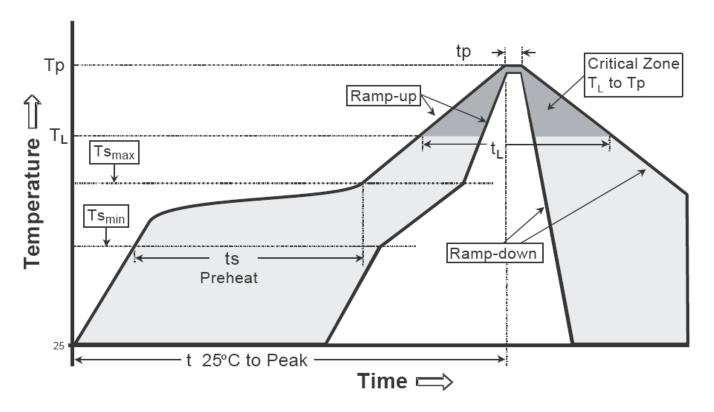
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#### Recommended wave soldering condition

Product	Peak Temperature	Soldering Time		
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds		

#### Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T∟)	183°C	217°C
- Time (t∟)	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>P</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

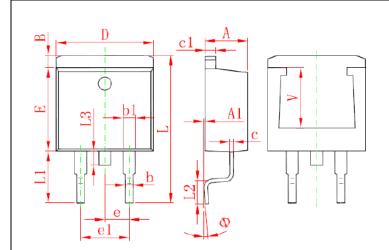
Note: All temperatures refer to topside of the package, measured on the package body surface.



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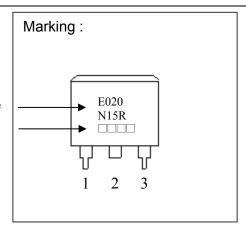
#### **TO-263 Dimension**



3-Lead Plastic Surface Mounted Package

CYStek Package Code: F3

Device Name
Date Code



Style: Pin 1.Gate 2.Drain 3.Source

Date Code(counting from left to right):

1st code: year code, the last digit of Christian year

 $2^{nd}$  code : month code, Jan $\rightarrow$ A, Feb $\rightarrow$ B, Mar $\rightarrow$ C, Apr $\rightarrow$ D May $\rightarrow$ E, Jun $\rightarrow$ F, Jul $\rightarrow$ G, Aug $\rightarrow$ H, Sep $\rightarrow$ J,

 $Oct \rightarrow K$ ,  $Nov \rightarrow L$ ,  $Dec \rightarrow M$ 

3<sup>rd</sup> and 4<sup>th</sup> codes: production serial number, 01~99

DIM	Millim	Millimeters		Inches		Millimeters		Inches	
DIIVI	Min.	Max.	Min.	Max.	DIM	Min.	Max.	Min.	Max.
Α	4.470	4.670	0.176	0.184	е	2.540	2.540 TYP		TYP
A1	0.000	0.150	0.000	0.006	e1	4.980	4.980 5.180		0.204
В	1.120	1.420	0.044	0.056	L	14.940	14.940 15.500		0.610
b	0.710	0.910	0.028	0.036	L1	4.950	4.950 5.450		0.215
b1	1.170	1.370	0.046	0.054	L2	2.340	2.340 2.740		0.108
С	0.310	0.530	0.012	0.021	L3	1.300	1.700	0.051	0.067
c1	1.170	1.370	0.046	0.054	Ф	0° 8°		0°	8°
D	10.010	10.310	0.394	0.406	V	6.400 REF		0.253	REF
Е	8.500	8.900	0.335	0.350					

Notes: 1. Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

#### Material:

• Lead : Pure tin plated.

• Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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# 全宇昕科技股份有限公司 CYStech Electronics Corp.

### **SGS TEST REPORT**

Package:	TO263(7L)
SGS Document no. :	ETR20C03576
Date:	2020/12/22



**AUTHORIZED SIGNAUTRE** 

OFFICE ADD: 13F-7, NO. 716, ZHONGZHENG RD., ZHONGHE DISTRICT,

NEW TAIPEI CITY, TAIWAN, 235-52 (FAR EAST CENTURY

PARK, BUILDING L)

TEL: (02) 8227-3826 FAX: (02) 8227-3830

http://www.cystekec.com/





**Test Report** 

號碼(No.): ETR20C03576 頁數(Page): 1 of 22 日期(Date): 22-Dec-2020

全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

以下測試樣品係由申請廠商所提供及確認 (The following sample(s) was/were submitted and identified by/on behalf of the applicant as):

全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.) 送樣廠商(Sample Submitted By)

樣品名稱(Sample Name) DFN SERIES · SOP SERIES · SOT SERIES · TO277 · TO251 · TO252 ·

TSOP-6 \ TO92(L) \ TO126(ML) \ TO220(FP) \ TO262 \ TO263(7L) \

DBS SAMESMX SERIES GEM2928-8J

\_\_\_\_\_\_

收件日(Sample Receiving Date) 15-Dec-2020

測試期間(Testing Period) 15-Dec-2020 to 22-Dec-2020

依據客戶要求進行測試,測試項目請參閱測試結果表格。(Testing item(s) is/are 測試需求(Test Requested)

specified by client. Please refer to result table for testing item(s).)

請參閱下一頁 (Please refer to following pages.) 測試結果(Test Results)







# **Test Report**

號碼(No.): ETR20C03576 日期(Date): 22-Dec-2020 頁數(Page): 2 of 22

全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

#### 測試部位敘述 (Test Part Description)

No.1 : 混測銀色金屬接腳鍍層 (MIXED PLATING LAYER OF SILVER COLORED METAL PIN)
No.2 : 混測銀色金屬接腳底材 (MIXED BASE MATERIAL OF SILVER COLORED METAL PIN)

No.3 : 混測銀色金屬 (含鍍層) (MIXED SILVER COLORED METAL (INCLUDING THE PLATING LAYER))

No.4 : 混測本體 (MIXED BODY)

#### 測試結果 (Test Results)

測試項目	測試方法	單位	MDL		結果	
(Test Items)	(Method)	(Unit)		No.1	(Result) No.2	No.3
鎘 (Cd) (Cadmium (Cd)) (CAS No.: 7440-43-9)	酸洗脫鍍層·參考IEC 62321-5: 2013· 以感應耦合電漿發射光譜儀分析。(IEC 62321-5: 2013 application of modified	mg/kg	2	n.d.		
鉛 (Pb) (Lead (Pb)) (CAS No.: 7439- 92-1)	digestion by surface etching, analysis was performed by ICP-OES.)	mg/kg	2	76.3		
汞 (Hg) (Mercury (Hg)) (CAS No.: 7439-97-6)	酸洗脫鍍層·參考IEC 62321-4: 2013+AMD1: 2017·以感應耦合電漿發射光譜儀分析。(IEC 62321-4: 2013+AMD1: 2017 application of modified digestion by surface etching, analysis was performed by ICP-OES.)	mg/kg	2	n.d.		
鎘 (Cd) (Cadmium (Cd)) (CAS No.: 7440-43-9)	參考IEC 62321-5: 2013 · 以感應耦合電 漿發射光譜儀分析。(With reference to	mg/kg	2		n.d.	
鉛 (Pb) (Lead (Pb)) (CAS No.: 7439- 92-1)	IEC 62321-5: 2013, analysis was performed by ICP-OES.)	mg/kg	2		6.94	
汞 (Hg) (Mercury (Hg)) (CAS No.: 7439-97-6)	參考IEC 62321-4: 2013 + AMD1: 2017 · 以感應耦合電漿發射光譜儀分析。(With reference to IEC 62321-4: 2013 + AMD1: 2017, analysis was performed by ICP-OES.)	mg/kg	2		n.d.	
六價鉻 (Hexavalent Chromium) Cr(VI) (CAS No.: 18540-29-9) (#2)	參考IEC 62321-7-1: 2015·以紫外光-可見光分光光度計分析。(With reference to IEC 62321-7-1: 2015, analysis was performed by UV-VIS.)	μg/cm²	0.1	n.d.	n.d.	

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新北市五股區新北產業園區五權七路 25 號 t+886(02)2299 3939 f+886(02)2299 3237 25, Wu Chyuan 7th Road, New Taipei Industrial Park, Wu Ku District, New Taipei City, Taiwan



# **Test Report**

號碼(No.): ETR20C03576 日期(Date): 22-Dec-2020

頁數(Page): 3 of 22

全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

測試項目	測試方法	單位	MDL		結果	
(Test Items)	(Method)	(Unit)			(Result)	
				No.1	No.2	No.3
一溴聯苯 (Monobromobiphenyl)		mg/kg	5			n.d.
二溴聯苯 (Dibromobiphenyl)		mg/kg	5			n.d.
三溴聯苯 (Tribromobiphenyl)		mg/kg	5			n.d.
四溴聯苯 (Tetrabromobiphenyl)		mg/kg	5			n.d.
五溴聯苯 (Pentabromobiphenyl)		mg/kg	5			n.d.
六溴聯苯 (Hexabromobiphenyl)		mg/kg	5			n.d.
七溴聯苯 (Heptabromobiphenyl)		mg/kg	5			n.d.
八溴聯苯 (Octabromobiphenyl)		mg/kg	5			n.d.
九溴聯苯 (Nonabromobiphenyl)		mg/kg	5			n.d.
十溴聯苯 (Decabromobiphenyl)	參考IEC 62321-6: 2015 · 以氣相層析儀/	mg/kg	5			n.d.
多溴聯苯總和 (Sum of PBBs)	質譜儀分析。(With reference to IEC	mg/kg	-			n.d.
一溴聯苯醚 (Monobromodiphenyl ether)	62321-6: 2015, analysis was performed	mg/kg	5			n.d.
二溴聯苯醚 (Dibromodiphenyl ether)	by GC/MS.)	mg/kg	5			n.d.
三溴聯苯醚 (Tribromodiphenyl ether)		mg/kg	5			n.d.
四溴聯苯醚 (Tetrabromodiphenyl ether)		mg/kg	5			n.d.
五溴聯苯醚 (Pentabromodiphenyl ether)		mg/kg	5			n.d.
六溴聯苯醚 (Hexabromodiphenyl ether)		mg/kg	5			n.d.
七溴聯苯醚 (Heptabromodiphenyl ether)		mg/kg	5			n.d.
八溴聯苯醚 (Octabromodiphenyl ether)		mg/kg	5			n.d.
九溴聯苯醚 (Nonabromodiphenyl ether)		mg/kg	5			n.d.
十溴聯苯醚 (Decabromodiphenyl ether)		mg/kg	5			n.d.
多溴聯苯醚總和 (Sum of PBDEs)		mg/kg	-			n.d.



# **Test Report**

號碼(No.): ETR20C03576 日期(Date): 22-Dec-2020

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全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

測試項目	測試方法	單位	MDL	結果		
(Test Items)	(Method)	(Unit)		(Result)		
				No.1	No.2	No.3
鄰苯二甲酸丁苯甲酯 (BBP) (Butyl benzyl phthalate (BBP)) (CAS No.: 85- 68-7)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.
鄰苯二甲酸二丁酯 (DBP) (Dibutyl phthalate (DBP)) (CAS No.: 84-74-2)	參考IEC 62321-8: 2017·以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.
鄰苯二甲酸二(2-乙基己基)酯 (DEHP) (Di-(2-ethylhexyl) phthalate (DEHP)) (CAS No.: 117-81-7)	參考IEC 62321-8: 2017·以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.
鄰苯二甲酸二異丁酯 (DIBP) (Diisobutyl phthalate (DIBP)) (CAS No.: 84-69-5)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.
鄰苯二甲酸二異癸酯 (DIDP) (Diisodecyl phthalate (DIDP)) (CAS No.: 26761-40-0, 68515-49-1)	參考IEC 62321-8: 2017·以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.
鄰苯二甲酸二異壬酯 (DINP) (Diisononyl phthalate (DINP)) (CAS No.: 28553-12-0, 68515-48-0)	參考IEC 62321-8: 2017·以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.
鄰苯二甲酸二正辛酯 (DNOP) (Di-n-octyl phthalate (DNOP)) (CAS No.: 117-84-0)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.
鄰苯二甲酸二正己酯 (DNHP) (Di-n-hexyl phthalate (DNHP)) (CAS No.: 84-75-3)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50			n.d.



# **Test Report**

號碼(No.): ETR20C03576 日期(Date): 22-Dec-2020

頁數(Page): 5 of 22 全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

測試項目 (Test Items)	測試方法 (Method)	單位 (Unit)	MDL	結果 (Result)
				No.4
鎘 (Cd) (Cadmium (Cd)) (CAS No.: 7440-43-9)	參考IEC 62321-5: 2013·以感應耦合電 漿發射光譜儀分析。(With reference to	mg/kg	2	n.d.
鉛 (Pb) (Lead (Pb)) (CAS No.: 7439- 92-1)	IEC 62321-5: 2013, analysis was performed by ICP-OES.)	mg/kg	2	3180
汞 (Hg) (Mercury (Hg)) (CAS No.: 7439-97-6)	參考IEC 62321-4: 2013+ AMD1: 2017· 以感應耦合電漿發射光譜儀分析。(With reference to IEC 62321-4: 2013+ AMD1: 2017, analysis was performed by ICP-OES.)	mg/kg	2	n.d.
六價鉻 Cr(VI) (Hexavalent Chromium Cr(VI)) (CAS No.: 18540-29-9)	參考IEC 62321-7-2: 2017·以紫外光-可 見光分光光度計分析。(With reference to IEC 62321-7-2: 2017, analysis was performed by UV-VIS.)	mg/kg	8	n.d.
一溴聯苯 (Monobromobiphenyl)		mg/kg	5	n.d.
二溴聯苯 (Dibromobiphenyl)		mg/kg	5	n.d.
三溴聯苯 (Tribromobiphenyl)		mg/kg	5	n.d.
四溴聯苯 (Tetrabromobiphenyl)	# */IFC COOOL C OOLF   N = 17 = 17 = 17 = 17 = 17 = 17 = 17 =	mg/kg	5	n.d.
五溴聯苯 (Pentabromobiphenyl)	參考IEC 62321-6: 2015 · 以氣相層析儀/	mg/kg	5	n.d.
六溴聯苯 (Hexabromobiphenyl)	質譜儀分析。(With reference to IEC 62321-6: 2015, analysis was performed	mg/kg	5	n.d.
七溴聯苯 (Heptabromobiphenyl)	by GC/MS.)	mg/kg	5	n.d.
八溴聯苯 (Octabromobiphenyl)	by GC/1013.7	mg/kg	5	n.d.
九溴聯苯 (Nonabromobiphenyl)		mg/kg	5	n.d.
十溴聯苯 (Decabromobiphenyl)		mg/kg	5	n.d.
多溴聯苯總和 (Sum of PBBs)		mg/kg	-	n.d.



# **Test Report**

號碼(No.): ETR20C03576 日期(Date): 22-Dec-2020

全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

測試項目 (Test Items)	測試方法 (Method)	單位 (Unit)	MDL	結果 (Result) No.4
一溴聯苯醚 (Monobromodiphenyl ether)		mg/kg	5	n.d.
二溴聯苯醚 (Dibromodiphenyl ether)		mg/kg	5	n.d.
三溴聯苯醚 (Tribromodiphenyl ether)		mg/kg	5	n.d.
四溴聯苯醚 (Tetrabromodiphenyl ether)	<b>************************************</b>	mg/kg	5	n.d.
五溴聯苯醚 (Pentabromodiphenyl ether)	參考IEC 62321-6: 2015·以氣相層析儀/ 質譜儀分析。(With reference to IEC	mg/kg	5	n.d.
六溴聯苯醚 (Hexabromodiphenyl ether)	貝語 展力が 。 (With reference to fec 62321-6: 2015, analysis was performed	mg/kg	5	n.d.
七溴聯苯醚 (Heptabromodiphenyl ether)	by GC/MS.)	mg/kg	5	n.d.
八溴聯苯醚 (Octabromodiphenyl ether)	) ( ) ( ) ( ) ( ) ( ) ( ) ( ) ( ) ( ) (	mg/kg	5	n.d.
九溴聯苯醚 (Nonabromodiphenyl ether)		mg/kg	5	n.d.
十溴聯苯醚 (Decabromodiphenyl ether)		mg/kg	5	n.d.
多溴聯苯醚總和 (Sum of PBDEs)		mg/kg	-	n.d.
鄰苯二甲酸丁苯甲酯 (BBP) (Butyl benzyl phthalate (BBP)) (CAS No.: 85- 68-7)	參考IEC 62321-8: 2017·以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.
鄰苯二甲酸二丁酯 (DBP) (Dibutyl phthalate (DBP)) (CAS No.: 84-74-2)	參考IEC 62321-8: 2017·以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.
鄰苯二甲酸二(2-乙基己基)酯 (DEHP) (Di-(2-ethylhexyl) phthalate (DEHP)) (CAS No.: 117-81-7)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.
鄰苯二甲酸二異丁酯 (DIBP) (Diisobutyl phthalate (DIBP)) (CAS No.: 84-69-5)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.
鄰苯二甲酸二異癸酯 (DIDP) (Diisodecyl phthalate (DIDP)) (CAS No.: 26761-40-0, 68515-49-1)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.

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# **Test Report**

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全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

測試項目 (Test Items)	測試方法 (Method)	單位 (Unit)	MDL	結果 (Result) No.4
鄰苯二甲酸二異壬酯 (DINP) (Diisononyl phthalate (DINP)) (CAS No.: 28553-12-0, 68515-48-0)	參考IEC 62321-8: 2017·以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.
鄰苯二甲酸二正辛酯 (DNOP) (Di-n-octyl phthalate (DNOP)) (CAS No.: 117-84-0)	參考IEC 62321-8: 2017 · 以氣相層析儀/ 質譜儀分析。(With reference to IEC 62321-8: 2017, analysis was performed by GC/MS.)	mg/kg	50	n.d.
六溴環十二烷及所有主要被辨別出的異構物 (HBCDD) ( $\alpha$ - HBCDD, $\beta$ - HBCDD, $\gamma$ - HBCDD) (Hexabromocyclododecane (HBCDD) and all major diastereoisomers identified ( $\alpha$ - HBCDD, $\beta$ - HBCDD, $\gamma$ - HBCDD)) (CAS No.: 25637-99-4, 3194-55-6 (134237-51-7, 134237-50-6, 134237-52-8))	參考IEC 62321: 2008·以氣相層析儀/質譜儀分析。(With reference to IEC 62321: 2008, analysis was performed by GC/MS.)	mg/kg	5	n.d.
氟 (F) (Fluorine (F)) (CAS No.: 14762-94-8)	參考BS EN 14582: 2016·以離子層析儀分析。(With reference to BS EN 14582: 2016, analysis was performed by IC.)	mg/kg	50	n.d.
氯 (Cl) (Chlorine (Cl)) (CAS No.: 22537-15-1)	参考BS EN 14582: 2016·以離子層析儀 分析。(With reference to BS EN 14582: 2016, analysis was performed by IC.)	mg/kg	50	n.d.
溴 (Br) (Bromine (Br)) (CAS No.: 10097-32-2)	參考BS EN 14582: 2016·以離子層析儀 分析。(With reference to BS EN 14582: 2016, analysis was performed by IC.)	mg/kg	50	n.d.
碘 (I) (Iodine (I)) (CAS No.: 14362-44- 8)	參考BS EN 14582: 2016·以離子層析儀分析。(With reference to BS EN 14582: 2016, analysis was performed by IC.)	mg/kg	50	n.d.



# **Test Report**

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全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

測試項目	測試方法	單位	MDL	結果
(Test Items)	(Method)	(Unit)		(Result)
				No.4
全氟辛烷磺酸及其鹽類 (PFOS and its	參考CEN/TS 15968: 2010 · 以液相層析	mg/kg	0.01	n.d.
salts) (CAS No.: 1763-23-1 and its	串聯質譜儀分析。(With reference to			
salts)	CEN/TS 15968: 2010, analysis was			
	performed by LC/MS/MS.)			
全氟辛酸及其鹽類 (PFOA and its salts)	參考CEN/TS 15968: 2010 · 以液相層析	mg/kg	0.01	n.d.
(CAS No.: 335-67-1 and its salts)	串聯質譜儀分析。(With reference to			
	CEN/TS 15968: 2010, analysis was			
	performed by LC/MS/MS.)			
四溴雙酚-A (TBBP-A)	參考RSTS-E&E-121 · 以液相層析儀/質	mg/kg	10	n.d.
(Tetrabromobisphenol A (TBBP-A))	譜儀分析。(With reference to RSTS-			
(CAS No.: 79-94-7)	E&E-121, analysis was performed by			
	LC/MS.)			
鄰苯二甲酸二正己酯 (DNHP) (Di-n-	參考IEC 62321-8: 2017 · 以氣相層析儀/	mg/kg	50	n.d.
hexyl phthalate (DNHP)) (CAS No.:	質譜儀分析。(With reference to IEC			
84-75-3)	62321-8: 2017, analysis was performed			
	by GC/MS.)			
銻 (Sb) (Antimony (Sb)) (CAS No.:	參考US EPA 3052: 1996 · 以感應耦合電	mg/kg	2	56.0
7440-36-0)	漿發射光譜儀分析。(With reference to			
	US EPA 3052: 1996, analysis was			
	performed by ICP-OES.)			
鈹 (Be) (Beryllium (Be)) (CAS No.:	參考US EPA 3052: 1996 · 以感應耦合電	mg/kg	2	n.d.
7440-41-7)	漿發射光譜儀分析。(With reference to			
	US EPA 3052: 1996, analysis was			
	performed by ICP-OES.)			
砷 (As) (Arsenic (As)) (CAS No.: 7440-	參考US EPA 3052: 1996 · 以感應耦合電	mg/kg	2	n.d.
38-2)	漿發射光譜儀分析。(With reference to			
	US EPA 3052: 1996, analysis was			
	performed by ICP-OES.)			

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# **Test Report**

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全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

#### 備註(Note):

- 1. mg/kg = ppm ; 0.1wt% = 1000ppm
- 2. MDL = Method Detection Limit (方法偵測極限值)
- 3. n.d. = Not Detected (未檢出); 小於MDL / Less than MDL
- 4. "-" = Not Regulated (無規格值)
- 5. "---" = Not Conducted (未測試項目)
- 6. 全氟辛烷磺酸及其鹽類包含 (PFOS and its salts including): CAS No.: 29081-56-9, 2795-39-3, 29457-72-5, 70225-14-8, 56773-42-3, 251099-16-8, 307-35-7.
- 7. 全氟辛酸及其鹽類包含 (PFOA and its salts including): CAS No.: 3825-26-1, 335-95-5, 2395-00-8, 335-93-3, 335-66-0.
- 8. (#2) =
  - a. 當六價鉻結果大於 $0.13~\mu g/cm^2$ ·表示樣品表層含有六價鉻。(The sample is positive for Cr(VI) if the Cr(VI) concentration is greater than  $0.13~\mu g/cm^2$ . The sample coating is considered to contain Cr(VI).) b. 當六價鉻結果為n.d. (濃度小於 $0.10~\mu g/cm^2$ )·表示表層不含六價鉻。(The sample is negative for Cr(VI) if Cr(VI) is n.d. (concentration less than  $0.10~\mu g/cm^2$ ). The coating is considered a non-Cr(VI) based coating) c. 當六價鉻結果介於 $0.10~\mu g/cm^2$  時·無法確定塗層是否含有六價鉻。(The result between  $0.10~\mu g/cm^2$  and  $0.13~\mu g/cm^2$  is considered to be inconclusive unavoidable coating variations may influence the determination.)
- 9. 樣品的測試是基於申請人要求混合測試,報告中的混合測試結果不代表其中個別單一材質的含量。
  The sample(s) was/were analyzed on behalf of the applicant as mixing sample in one testing. The above result(s) was/were only given as the informality value.



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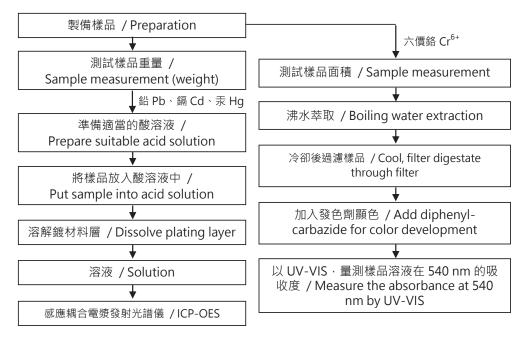
全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

#### No.1

#### 鍍層重金屬測試流程圖 / Flow Chart of Stripping method for metal analysis

根據以下的流程圖之條件,樣品之外部鍍層已完全溶解。( 六價鉻測試方法除外 ) / The plating layer of samples were dissolved totally by pre-conditioning method according to below flow chart. ( $Cr^{6+}$  test method excluded)





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全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

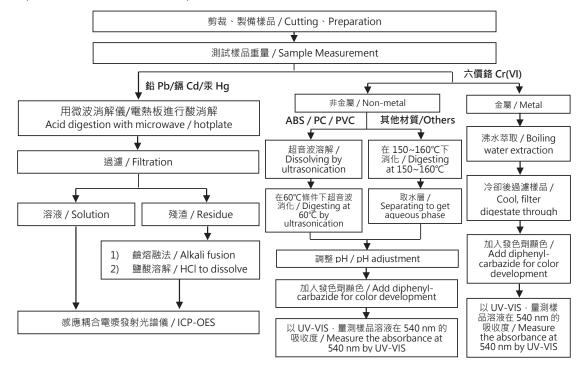
235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

No.2, 4

#### 重金屬流程圖 / Analytical flow chart of Heavy Metal

根據以下的流程圖之條件,樣品已完全溶解。(六價鉻測試方法除外)

These samples were dissolved totally by pre-conditioning method according to below flow chart. ( $Cr^{6+}$  test method excluded)





# **Test Report**

號碼(No.): ETR20C03576

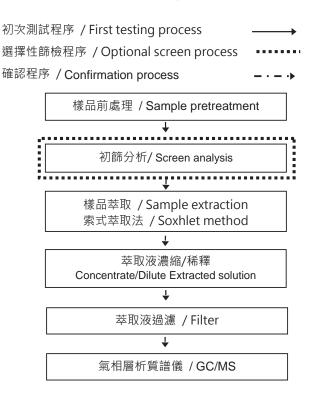
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全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

#### 多溴聯苯/多溴聯苯醚分析流程圖 / Analytical flow chart - PBBs/PBDEs





# **Test Report**

號碼(No.): ETR20C03576

日期(Date): 22-Dec-2020

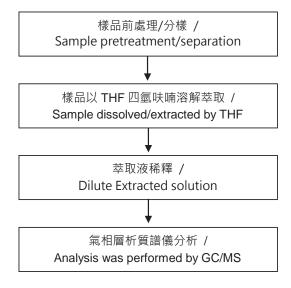
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#### 可塑劑分析流程圖 / Analytical flow chart - Phthalate

#### 【測試方法/Test method: IEC 62321-8】





# **Test Report**

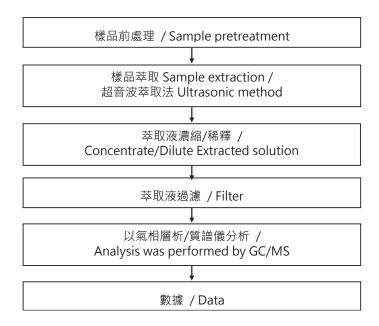
號碼(No.): ETR20C03576 日期(Date): 22-Dec-2020

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#### 六溴環十二烷分析流程圖 / Analytical flow chart - HBCDD





# **Test Report**

號碼(No.): ETR20C03576

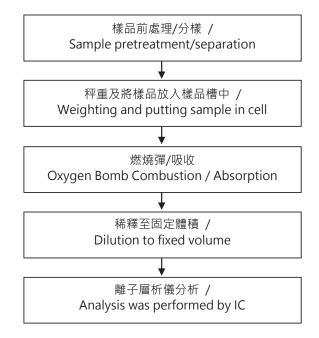
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#### 鹵素分析流程圖 / Analytical flow chart - Halogen





# **Test Report**

號碼(No.): ETR20C03576

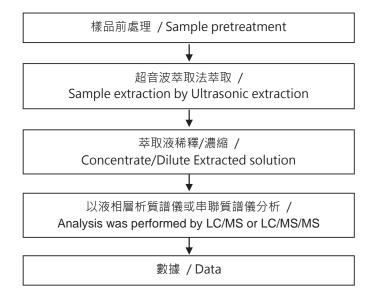
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235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

#### 全氟辛酸/全氟辛烷磺酸分析流程圖 / Analytical flow chart - PFOA/PFOS





# **Test Report**

號碼(No.): ETR20C03576

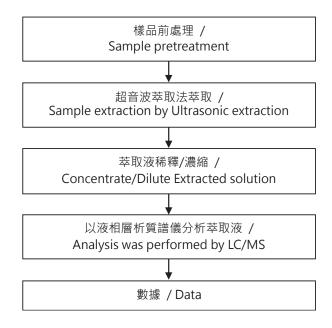
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235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

#### 四溴雙酚-A 分析流程圖 / Analytical flow chart - TBBP-A





# **Test Report**

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全宇昕科技股份有限公司 (CYSTECH ELECTRONICS CORP.)

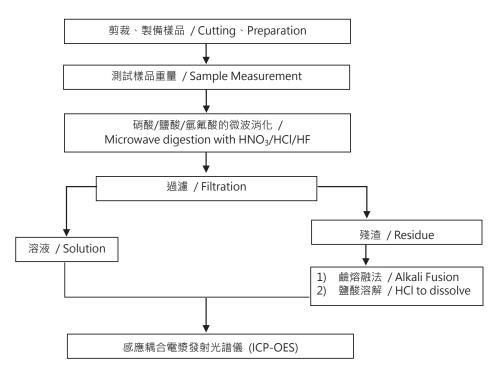
235-52新北市中和區中正路716號15F之7(遠東世紀廣場L棟) (15F-7, NO.716, ZHONGZHENG RD, ZHONGHE DISTRICT, NEW TAIPEI CITY 235-52, TAIWAN (FAR EAST CENTURY PARK, BUILDING L))

#### 重金屬流程圖 / Analytical flow chart of Heavy Metal

根據以下的流程圖之條件,樣品已完全溶解。

These samples were dissolved totally by pre-conditioning method according to below flow chart.

【参考方法/Reference method: US EPA 3051、US EPA 3052】



\* US EPA 3051 方法未添加氫氟酸 / US EPA 3051 method does not add HF.



# **Test Report**

號碼(No.): ETR20C03576 日期(Date): 22-Dec-2020

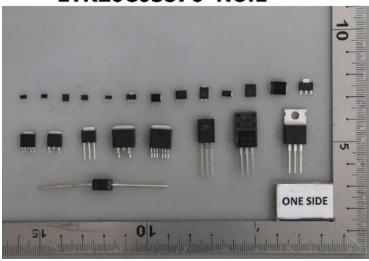
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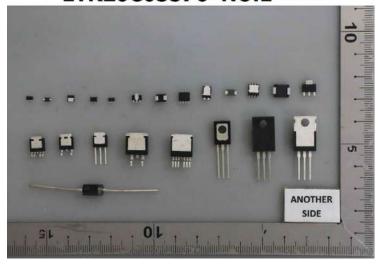
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\* 照片中如有箭頭標示,則表示為實際檢測之樣品/部位. \* (The tested sample / part is marked by an arrow if it's shown on the photo.)

#### ETR20C03576 NO.1



#### ETR20C03576 NO.1



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**Test Report** 

號碼(No.): ETR20C03576 日期

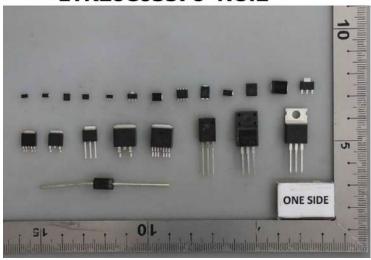
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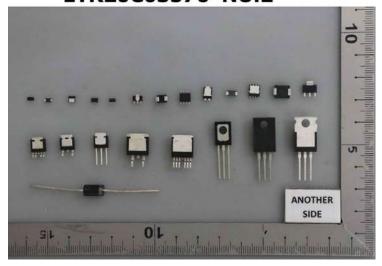
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#### ETR20C03576 NO.2



#### ETR20C03576 NO.2





**Test Report** 

號碼(No.): ETR20C03576

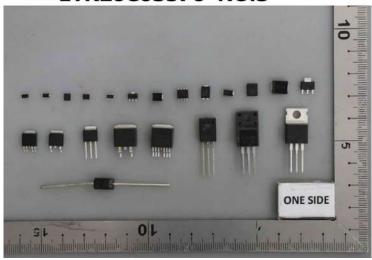
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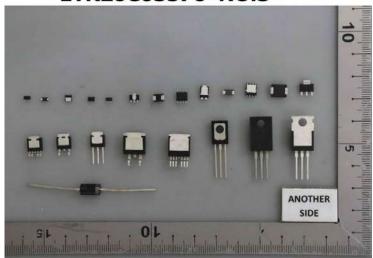
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#### ETR20C03576 NO.3



#### ETR20C03576 NO.3





# **Test Report**

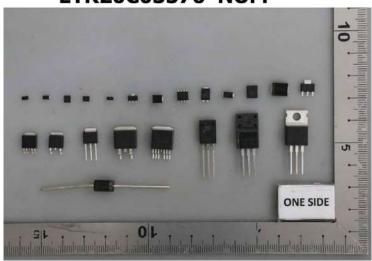
號碼(No.): ETR20C03576 日期(Date): 22-De

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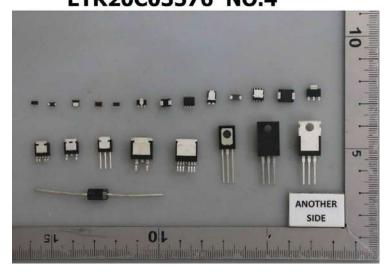
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#### ETR20C03576 NO.4



#### ETR20C03576 NO.4



\*\* 報告結尾 (End of Report) \*\*

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# 全宇昕科技股份有限公司

### **CYStech Electronics Corp.**

# 信賴性試驗報告 RELIABILITY TEST REPORT

Package: TO-263

Part No.: MTE020N10RF3

**Document No:** 1803-028-1

Date: 2018/3/14

制作	審核	核准
葉秀娥	去如美	更振覺



**AUTHORIZED SIGNAUTRE** 

15F-7, No. 716, Chung Cheng Rd., Chung Ho City, Taipei Hsien, Taiwan, 235-52 (Far East Century Park. Building L) , Tel: +886-2-8227-3826 , Fax: +886-2-8227-3830, <a href="http://www.cystek.com.tw">http://www.cystek.com.tw</a>

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# 全宇昕科技股份有限公司

#### **CYStech Electronics Corp.**

#### 信賴性試驗報告 RELIABILITY TEST REPORT

包裝別 Package:	TO-263	日期 Date:	2018/3/14
品名 Part no.:	MTE020N10RF3	文件編號 Document no.:	1803-028-1
數量 Q'ty:	330 PCS	製表者 Prepared by:	葉秀娥

#### 試驗目的:新封裝評估實驗

#### 一、試驗結果 Test Result:

試驗項目	試驗條件	樣品數	試驗時間	累積實驗時間	不良數	FIT	MTTF	結果	備註
Test Item	Test Condition	Sample	Test Time	CUM. Time	Failure		(yr)	Result	Remark
		Size	hrs/cyc	hrs.	Q'ty				
高溫儲存試驗 (HTS) High Temp. Storage	Ta=175°C	77	1000hrs	77000	0	65.1	1752.8	ACC	
高溫高濕儲存試驗 (WHTS) Wet High Temp. Storage	Ta=85°C , RH=85%	77	1000hrs	77000	0	1140.1	100.1	ACC	
壓力鍋試驗 (PCT) Pressure Cooker Test	Continuous storage Atmospheres Ta=121±2°C, P=15psig, RH=100%RH	77	168hrs	12936	0	309.7	368.6	ACC	
動作壽命試驗 (OPL) Operating Life Test	Ta=25°C ,PD*max	22	1000hrs	22000	0	775.5	147.2	ACC	
冷熱衝擊試驗 (TST) Thermal Shock Test	5Minutes dwell time $-65^{\circ}\text{C} \sim 175^{\circ}\text{C}$	77	200cys	2567	0	-	-	ACC	

二、結論 Conclusion: 以上試驗OK.

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#### MTE020N10RF3 電性CPK品質檢驗報告

	MTE020N10RF3 電性CPK品質檢驗報告								
項	次	1	2	3	4	5	6	7	
測試	參數	BVDSS	VTH	+IGSS	-IGSS	IDSS	RDON	VFSD	
參數	條件	ID=250uA	ID=250uA	VGS=20V	VGS=-20V	VDS=80V	ID=20A	IS=20A	
							VGS=10V		
規格	上限		4	100	100	1	30	1.2	
規格	下限	100	2						
		V	V	nA	nA	uA	mΩ	V	
	1	118.9	3.05	7.80	6.50	0.029	26.85	0.928	
	2	119.0	3.10	4.90	6.90	0.029	25.82	0.927	
	3	118.6	3.48	6.50	6.10	0.028	25.14	0.927	
	4	118.4	3.36	6.10	5.80	0.027	26.05	0.928	
	5	118.5	2.99	6.00	5.20	0.026	27.13	0.927	
	6	118.6	2.95	5.00	6.00	0.027	26.02	0.926	
	7	118.6	2.98	6.10	6.10	0.026	25.25	0.925	
實	8	118.7	2.99	5.90	5.30	0.028	24.96	0.925	
	9	118.6	2.98	5.40	6.30	0.028	24.97	0.925	
	10	118.6	3.04	6.50	6.50	0.028	24.82	0.925	
	11	118.3	3.28	6.70	5.90	0.029	24.99	0.927	
	12	118.4	3.10	6.40	6.30	0.028	24.91	0.926	
	13	118.6 118.6	3.13	6.50 5.30	5.70 6.90	0.029	24.37	0.926	
	15	118.4	3.32	6.20	5.80	0.029	24.30 24.93	0.925	
	16	118.4	3.43	6.60	6.70	0.029	25.68	0.927	
	17	118.9	3.02	5.10	6.50	0.023	26.94	0.926	
	18	118.9	2.98	5.90	5.70	0.028	26.02	0.925	
	19	119.0	2.96	4.60	6.10	0.027	25.31	0.925	
	20	118.9	3.01	4.60	6.10	0.026	25.21	0.924	
	21	119.0	2.96	4.90	5.70	0.024	25.36	0.925	
	22	119.0	2.97	5.70	6.10	0.024	25.98	0.925	
	23	118.9	3.14	6.00	6.30	0.026	25.30	0.926	
	24	119.0	3.49	5.30	6.00	0.027	24.97	0.927	
測	25	118.9	3.56	5.70	5.50	0.024	25.25	0.928	
	26	118.8	3.35	5.70	5.50	0.024	25.56	0.928	
	27	118.9	2.91	4.70	6.10	0.025	28.09	0.926	
	28	119.0	2.93	4.80	6.00	0.026	27.15	0.928	
	29	119.0	2.90	5.80	5.80	0.026	25.93	0.925	
	30	119.0	2.96	5.70	6.20	0.026	25.63	0.926	
	31	118.9	3.08	6.20	6.10	0.026	25.07	0.926	
	32	118.9	3.29	5.60	5.70	0.025	25.04	0.928	
	33	118.8	3.51	5.50	5.40	0.025	25.04	0.928	
	34	118.7	3.60	5.60	5.40	0.025	25.32	0.929	
	35	119.1	3.15	5.50	5.00	0.025	24.43	0.925	
	36	119.1	3.05	5.60	6.10	0.025	24.62	0.924	
	37	119.1	3.10	5.70	5.50	0.025	24.60	0.925	
	38	119.0	3.25	5.80	6.00	0.026	24.55	0.924	
	39	119.0	3.49	5.10	5.30	0.026	24.72	0.926	
	40	118.9	3.51	5.30	5.70	0.026	25.06	0.926	
炐	41	118.8 119.0	3.67 3.40	5.30	6.10	0.027	25.68 24.91	0.927	
值	42	119.0	3.40	5.30	6.30	0.027	24.91	0.926	
	44	119.1	3.26	5.50	6.00	0.027	24.94	0.926	
	45	119.0	3.30	4.30	6.00	0.025	24.79	0.926	
	46	118.9	3.33	4.30	5.80	0.023	24.75	0.926	
	47	118.9	3.53	3.80	5.80	0.024	24.86	0.927	
	48	118.8	3.57	4.40	5.60	0.024	25.25	0.928	
	49	118.8	3.54	3.90	5.80	0.023	25.96	0.929	
	50	118.8	3.43	4.20	5.90	0.024	25.71	0.929	
M	AX	119.10	3.67	7.80	6.90	0.029	28.09	0.929	
М	IN	118.30	2.90	3.80	5.00	0.023	24.30	0.924	
Х-	bar	118.83	3.21	5.49	5.94	0.026	25.38	0.926	
標準	達差	0.206	0.226	0.787	0.408	0.002	0.783	0.001	